Supplementary Information for

Graphene meta-interface for enhancing the stretchability of brittle oxide layers

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S1. Derivation of the shear-lag model

Strain transfer between the PET substrate and the ITO layer via the graphene layer can be described using the 2D shear lag model of McGuigan *et al.*³² The governing equation is derived from the force equilibrium relating the interfacial shear stress $\tau(x)$ of the graphene layer to the tensile stress σ transferred to the ITO layer; i.e.,

$$q\frac{d\sigma(x)}{dx} = -\tau(x)$$
(S1)

The shear stress in the multilayer graphene is given by

$$\tau(x) = \frac{G(\varepsilon x - \emptyset(x))}{p}$$
(S2)

when $x \le x_p$ and

$$\tau(x) = G\gamma_p = \tau_p \tag{S3}$$

when $x \ge x_p$, where $\Phi(x)$ is the displacement of the ITO layer, ε is the applied strain and γ_p is the plastic shear strain in the multilayer graphene at which the shear stress reaches the critical value τ_p at $x = x_p$. Because the strain is the gradient of the displacement, we have

$$\sigma(x) = E \frac{d\phi(x)}{dx},$$
(S4)

Combining Eqs. (S1) with (S2) yields the following differential equation:

$$\frac{d^2\phi}{dx^2} - \beta^2 \phi(x) = -\beta^2 \varepsilon x$$
(S5)

where $\beta = \sqrt{G/pqE}$. The following two boundary conditions are required to solve Eq. (S5):

$$\phi(x=0) = 0 \tag{S6}$$

and

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$$\sigma(a) = E \frac{d\phi(x)}{dx}_{(x=a)} = 0.$$
 (S7)

The solution to Eq. (S5) is given by

$$\phi(x) = \varepsilon \left(x - \frac{\sinh(\beta x)}{\beta \cosh(\beta a)} \right).$$
(S8)

The maximum stress occurs in the center of each segment, and we look for a solution where this stress is equal to the tensile strength σ^* , which corresponds to the maximum length of the segment before fracture at that strain. The tensile stress in the center of a segment is given by

$$\sigma(0) = \frac{1}{q} \int_0^a \tau(x) dx.$$
 (S9)

Substitution of Eqs. (S2) and (S3) into Eq. (S9) leads to the following expressions for the crack density *n* as a function of strain.

① The fully elastic case $(x_p > a)$

When maximum stress reaches the tensile strength, a is equal to half the maximum crack length; i.e.,

$$\sigma(0) = \frac{1}{q} \int_0^a \tau(x) dx = \sigma^*$$
(S10)

and we have

$$a = \frac{1}{\beta} \cosh^{-1} \left(\frac{1}{1 - \frac{\sigma^*}{\varepsilon E}} \right).$$
(S11)

Because the crack density is now given by n = 1/2a, we have

$$n = \frac{1}{2a} = \sqrt{\frac{G}{E}} \left[2\sqrt{pq}\cosh^{-1}\left(\frac{1}{1 - \frac{\sigma^*}{\varepsilon E}}\right) \right]^{-1}$$
(S12)

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② The elastic–plastic case $(x_p < a)$

When $x < x_p$, Eq. (S11) can be used for a; i.e.,

$$\tau(x) = \frac{G}{p\beta} \left(\varepsilon - \frac{\sigma^*}{E} \right) \sinh(\beta x)$$
(S13)

and when $x \ge x_p$ we have

$$\tau(x_p) = G\gamma_p. \tag{S14}$$

Because we require that the shear stress is continuous at $x=x_p$, we obtain

$$x_{p} = \frac{1}{\beta} \sinh^{-1} \left(\frac{\gamma_{p} \sqrt{\frac{Gp}{qE}}}{\left(\varepsilon - \frac{\sigma^{*}}{E}\right)} \right),$$
(S15)

and *a* is equal to half of the maximum crack length when the maximum stress becomes equal to the tensile strength. We therefore have

$$\sigma(0) = \frac{1}{q} \int_{0}^{a} \tau(x) dx = \frac{1}{q} \left(\int_{0}^{x_{p}} \tau(x) dx + \int_{x_{p}}^{a} G \gamma_{p} dx \right) = \sigma^{*},$$
(S16)

which leads to

$$a = \frac{Eq}{G\gamma_p} \left[\left(\frac{\sigma^*}{E} - \varepsilon \right) \cosh \left(\sinh^{-1} \left(\frac{\gamma_p \sqrt{\frac{Gp}{Eq}}}{\left(\varepsilon - \frac{\sigma^*}{E} \right)} \right) \right) + \varepsilon + \gamma_p \sqrt{\frac{GP}{Eq}} \sinh^{-1} \left(\frac{\gamma_p \sqrt{\frac{Gp}{Eq}}}{\left(\varepsilon - \frac{\sigma^*}{E} \right)} \right) \right].$$
(S17)

Because the crack density is n = 1/2a, this can be expressed as follows:

$$n = \frac{G\gamma_p}{2Eq} \left[\left(\frac{\sigma^*}{E} - \varepsilon \right) \cosh \left(\sinh^{-1} \left(\frac{\gamma_p \sqrt{\frac{Gp}{Eq}}}{\left(\varepsilon - \frac{\sigma^*}{E} \right)} \right) \right] + \varepsilon + \gamma_p \sqrt{\frac{GP}{Eq}} \sinh^{-1} \left(\frac{\gamma_p \sqrt{\frac{Gp}{Eq}}}{\left(\varepsilon - \frac{\sigma^*}{E} \right)} \right) \right]^{-1}$$
(S18)



Figure S1. Schematic of an off-axis RF magnetron sputtering.



Figure S2. Raman spectra (excitation wavelength $\lambda = 514$ nm) of the ITO/MLG after subtracting the peaks of PET substrates. The existence of the D peak indicates the damage on the graphene layers during ITO sputtering, but even with this damage, the graphene meta-interface can reduce the strain transfer by the interlayer sliding. By decreasing the sputtering damage of graphene, the performance of the graphene meta-interface can be improved further.



Figure S3. Transmittances of type-I and type-II structures over a range of wavelength.

Samples		Transmittance (%)	
		Mean	Standard deviation
Type-I	ITO	80.7	0.86
Type- II	ITO/2L G	76.6	0.57
	ITO/3L G	74.5	0.18
	ITO/4L G	74.1	0.64
	ITO/5L G	72.1	0.69

Table S1. Transmittances of type-I and type-II structures at a wavelength of 550 nm.



Figure S4. XRD diffraction patterns of ITO and ITO/graphene on the PET substrates.



Figure S5. Topographies of ITO and ITO/2LG on PET substrates.



Figure S6. Crack densities and the normalized electrical resistance for the ITO/1LG. a) Crack densities for the ITO/1LG, type-I and type-II structures as a function of the strain. b) The normalized electrical resistance of the ITO/1LG, type-I and type-II structures as a function of the strain.